



SOD-323 Schottky Barrier Diode 肖特基势垒二极管

■ **Internal Configuration & Device Marking 内部结构与产品打标**

Type 型号	BAT46WS	
Pin 管脚		
Mark 打标	S9	

■ **Absolute Maximum Ratings 最大额定值**

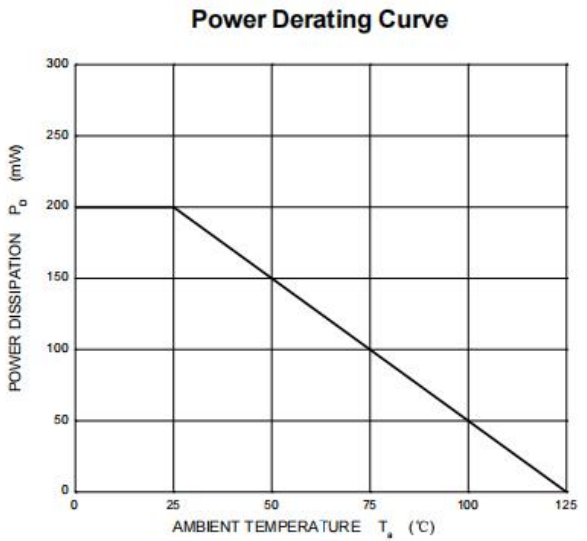
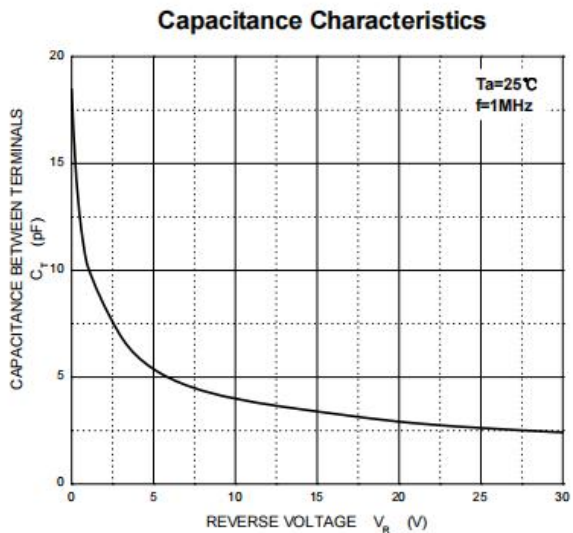
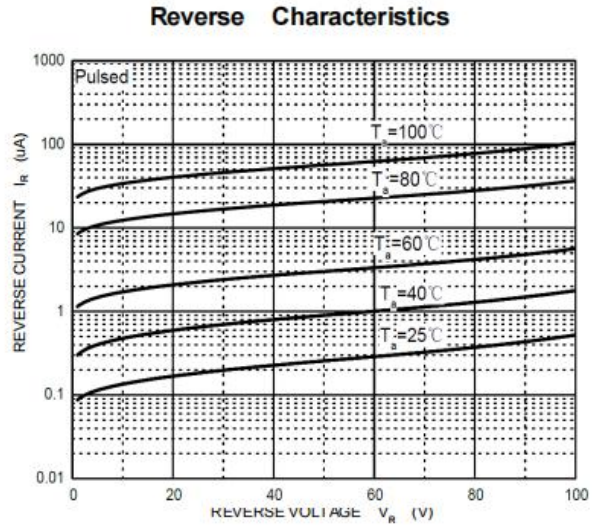
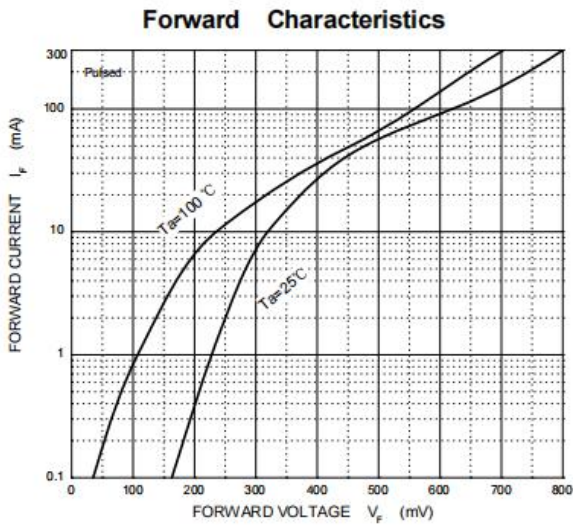
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
Forward Work Current 正向工作电流	$I_F(I_O)$	150	mA
Repetitive Peak Forward Current 重复正向峰值电流	I_{FRM}	350	mA
Surge Peak Forward Current 正向峰值浪涌电流	I_{FSM}	750	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	$^\circ C/W$
Junction Temperature 结温	T_J	-40to+125 $^\circ C$	
Storage Temperature 储藏温度	T_{stg}	-55to+150 $^\circ C$	

■ **Electrical Characteristics 电特性**

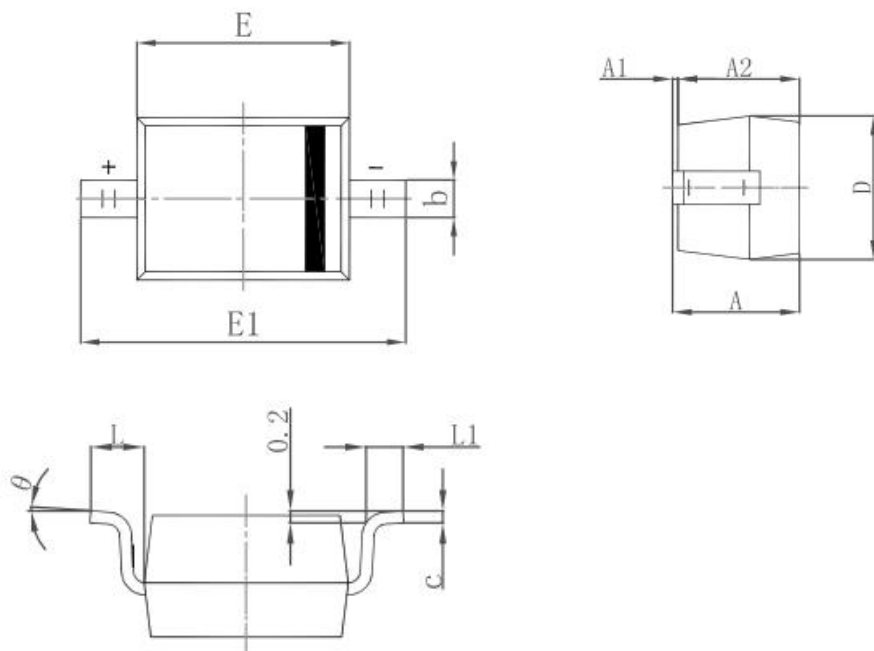
($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 25 $^\circ C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu A$)	$V_{(BR)}$	100	—	V
Reverse Leakage Current($V_R=10V$) 反向漏电流($V_R=50V$) ($V_R=75V$)	I_R	—	0.5 1 2	μA
Forward Voltage($I_F=0.1mA$) 正向电压($I_F=10mA$) ($I_F=250mA$)	V_F		0.25 0.45 1	V
Diode Capacitance($V_R=0V, f=1MHz$) 二极管电容($V_R=1V, f=1MHz$)	C_D	—	20 12	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		1.100		0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.000	0.031	0.039
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.750	0.098	0.108
L	0.475 REF		0.019 REF	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°